

O I P E

## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

JUL 20 2006

U.S. PATENT &amp; TRADEMARK OFFICE

Docket Number (Optional)	Application Number
FIS920040116US1	10/710,244
Applicant(s)	
Hui long Zhu	

Applicant(s)

Hui long Zhu

Filing Date

06/29/2004

Group Art Unit

2811

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Pg		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al.			
		4,853,076	8-1-89	Tsaur, et al.			
		4,855,245	8-8-89	Neppl, et al.			
↓		4,952,524	8-28-90	Lee, et al.			

## U.S. PATENT APPLICATION PUBLICATIONS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Pg		US 2001/0009784 A1	7-26-01	Ma, et al.			
		US 2002/0063292 A1	5-30-02	Armstrong, et al.			
		US 2002/0074598 A1	6-20-02	Doyle, et al.			
↓		US 2002/0086472	7-4-02	Roberds, et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							VIS	NO
Pg		JP64-76755	03-1989	Japan				

## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Page, Etc.)

Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.

Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.

EXAMINER

Pm from HDPN

DATE CONSIDERED

09/29/01

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Applicant(s) Huilong Zhu	
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**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
K		4,958,213	9-18-90	Eklund, et al.			
		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
V		5,108,843	4-28-92	Ohtaka, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
P		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeb, et al.			
V		US 2003/0040158 A1	2-27-03	Saitoh			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

PS  
Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress." International Electron Devices Meeting, 34.4.1, IEEE, September 1999.

↓  
P. Ootaka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

EXAMINER

DATE CONSIDERED

09/29/04

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Docket Number (Optional) F15920040116US1	Application Number 10/710,244
Applicant(s) Huilong Zhu	
Filing Date 06/29/2004	Group Art Unit 2811

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
R		5,134,085	7-28-92	Gilgen, et al.			
		5,310,446	5-10-94	Konishi, et al.			
		5,354,695	10-11-94	Leedy			
		5,371,399	12-6-94	Burroughes, et al.			
W		5,391,510	2-21-95	Hsu, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
R		US 2003/0057184 A1	3-27-03	Yu, et al.			
		US 2003/0067035 A1	4-10-03	Tews, et al.			
		US 2004/0113174 A1	6-17-2004	Chidambaram et al.			
W		US 2004/0113217 A1	6-17-2004	Chidambaram et al.			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

R		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and Its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
W		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

EXAMINER	DATE CONSIDERED
<i>J. Miller ROM (RDP)</i>	<i>09/29/06</i>

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				Applicant(s) Hui long Zhu			
				Filing Date 06/29/2004	Group Art Unit 2811		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
<i>B</i>		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelier			
<i>✓</i>		5,565,697	10-15-96	Asakawa, et al.			
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
<i>B</i>		US 2004/0238914 A1	12-2-2004	Deshpande et al.			
		US 2004/0262784 A1	12-30-2004	Doris et al.			
		US 2005/0040460 A1	2-24-2005	Chidambaram et al.			
<i>✓</i>		US 2005/0082634 A1	4-21-2005	Doris et al.			
<b>FOREIGN PATENT DOCUMENTS</b>							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
<i>B</i>		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.					
<i>✓</i>		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.					
EXAMINER	<i>John Bone LARSON</i>			DATE CONSIDERED		<i>09/29/04</i>	
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) EIS920040116US1	Applicant(s) Huilong Zhu	Application Number 10/710,244	
				Filing Date 06/29/2004	Group Art Unit 2811		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Y		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schetzina			
		5,679,965	10-21-97	Schetzina			
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Y		US 2005/0093030 A1	5-5-2005	Doris et al.			
		US 2005/0098829 A1	5-12-2005	Doris et al.			
		US 2005/0106799 A1	5-19-2005	Doris et al.			
		US 2005/0145954 A1	7-7-2005	Zhu et al.			
<b>FOREIGN PATENT DOCUMENTS</b>							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Trademarks	
						YES	NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
Y		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.					
Y		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.					
EXAMINER <i>[Signature]</i>				DATE CONSIDERED <i>09/29/96</i>			
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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
R		5,683,934	11-4-97	Candelaria			
		5,840,593	11-24-98	Leedy			
		5,861,651	1-19-99	Brasen, et al.			
		5,880,040	3-9-99	Sun, et al.			
↓		5,940,716	8-17-99	Jin, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
V		US 2005/0148146 A1	7-7-2005	Doris et al.			
		US 2005/0194699 A1	9-8-2005	Belyansky et al.			
		US 2005/0236668 A1	10-27-2005	Zhu et al.			
↓		US 2005/0245017 A1	11-3-2005	Belyansky et al.			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages, Etc.)

R | | S.R. Sheog, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing," Pp. 14-15.

R | | Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors," Pp. 1-5.

EXAMINER

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89/29/01

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**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
B		5,940,736	8-17-99	Brady, et al.			
		5,946,559	8-31-99	Leedy			
		5,960,297	9-28-99	Sakl			
		5,989,978	11-23-99	Peldous			
		6,008,126	12-28-99	Leedy			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
B		US 2006/0060925 A1	3-23-2006	Doris et al.			
		US 2005/0280051 A1	12-22-2005	Chidambaram et al.			
		US 2005/0282325 A1	12-22-2005	Belyansky et al.			
		US 2006/0027868 A1	2-9-2006	Doris et al.			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.

H. Warzer, et al., "Annealing of Degraded nppn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.

EXAMINER

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09/29/06

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**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RL		6,025,280	2-15-00	Brady, et al.			
		6,046,464	4-4-00	Schetzina			
		6,066,545	5-23-00	Doshi, et al.			
		6,090,684	7-18-00	Ishitsuka, et al.			
↓		6,107,143	8-22-00	Park, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
RL		US 2006/0057787 A1	3-16-2006	Doris et al.			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS**

*(Including Author, Title, Date, Pertinent Pages, Etc.)*

RL  
B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs," IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.

↓  
H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS," IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

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*[Signature]*  
RL  
Rene Tropor

DATE CONSIDERED

*09/29/06*

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#### U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
N		6,117,722	9-12-00	Woo, et al.			
		6,133,071	10-17-00	Nagai			
		6,165,383	12-26-00	Chou			
		6,221,735	4-24-01	Manley, et al.			
↓		6,228,694	5-8-01	Doyle, et al.			

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#### FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

#### OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

M		M. Khater, et al., "SiGe HBT Technology with $P_{max}/P_t = 350/300$ GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.
H		J.C. Bean, et al., "GEx Si 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.

EXAMINER	<i>MM PBM DPL</i>	DATE CONSIDERED
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				<b>U.S. PATENT DOCUMENTS</b>			
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
H		6,246,095	6-12-01	Brady, et al.			
L		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
V		6,274,444	8-14-01	Wang			
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Treatment YES      NO
<b>OTHER DOCUMENTS</b> <i>(including Author, Title, Date, Pertinent Pages, Etc.)</i>							
R		J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.					
J		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.					
EXAMINER <i>GJM from trepca</i>			DATE CONSIDERED <i>07/29/01</i>				
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<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
R		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-20-01	Akatsu, et al.			
✓		6,361,885	3-26-02	Chon			
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Permanent Pages, Etc.)</i>							
R		Subramanian S. Iyer, et al., "Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064.					
↓		R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050.					
EXAMINER <i>SJM PMB Grgan</i>			DATE CONSIDERED <i>09/29/02</i>				
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K		6,362,082	3-26-02	Doyle, et al.			
		6,368,931	4-9-02	Kuhn, et al.			
		6,403,486	6-11-02	Lou			
		6,403,975	6-11-02	Brunner, et al.			
		6,406,973	6-18-02	Lee			

**U.S. PATENT APPLICATION PUBLICATIONS**

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						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

P  
D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x Ge Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462.

Q. Ouyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000 IEEE, pp. 151-154.

EXAMINER

*John D. Parker*

DATE CONSIDERED

*09/29/01*

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				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>f</i>		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
<i>WV</i>		6,498,358	12-24-02	Lach, et al.			
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Traducción
							YES NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
EXAMINER	<i>S. M. John Oppen</i>			DATE CONSIDERED	<i>09/29/02</i>		
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R		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
		6,531,369	3-11-03	Ozkan, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

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**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

EXAMINER	<i>John Rom Feder</i>	DATE CONSIDERED	<i>09/29/06</i>
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Docket Number (Optional) FIS920040116US1	Application Number 10/710,244
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Filing Date 06/29/2004	Group Art Unit 2811

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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

EXAMINER	DATE CONSIDERED
<i>Beth Anne Taylor</i>	<i>07/29/04</i>

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				Applicant(s) Huilong Zhu			
				Filing Date 06/29/2004	Group Art Unit 2811		
				<b>U.S. PATENT DOCUMENTS</b>			
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R		6,825,529	11-30-2004	Chidambarrao et al.			
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<b>FOREIGN PATENT DOCUMENTS</b>							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
							YES
							NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
EXAMINER <i>[Signature]</i>				DATE CONSIDERED <i>09/29/06</i>			
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